

(146) US-20030109093-A1.DID. (((charge near3 (strap\$4 trap\$4 nitride))
(147) (((charge near3 (strap\$4 trap\$4 nitride))
(148) (((charge near3 (strap\$4 trap\$4 nitride))
(4) "20030109093" 6,670,671.pn.
(4792184) conduct\$4 metal
(8738) (((insulat\$5 dielectric oxide)) near4 (oxidizing oxidized) with (conduct\$4 me
(145546) first adj2 (conduct\$4 metal))
(477) (first adj2 (conduct\$4 metal) with (((insulat\$5 dielectric oxide)
(0) ((first adj2 (conduct\$4 metal) with (((insulat\$5 dielectric oxide)
(21) ((first adj2 (conduct\$4 metal) with (((insulat\$5 dielectric oxide)
(80) ((((insulat\$5 dielectric oxide)
(5749) bird adj beak
(5749) bird\$2 adj beak
(110) (bird adj beak) and ((sonos monos mnos)))
(38) ((bird adj beak)
(18) (((insulat\$5 dielectric oxide)
(2) 6645801.pn.
(2) 6645801.pn. and ((wordline "WL" ((word digit control adj gate) adj line) (word ne
(260209) (s7icid\$4 silicat\$4)
(2) 6645801.pn. and ((s7icid\$4 silicat\$4)
(2) 6524913.pn.
(3) diffusion near5 ion adj implantation
(5553) diffusion near5 ion adj implantation
(4059053) (source near drain source adj drain drain adj source s/d d/s active adj regi
(820) (diffusion near5 ion adj implantation) with ((source near drain source adj drain
(4024982) (source near drain source adj drain drain adj source s/d d/s)

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Plurals
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(((charge near3 (strap\$4 trap\$4 nitride))
) same ((bl bitline bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line)
(word near (read\$3 writ\$3))
) and ((sonos monos mnos)
) not (((charge near3 (strap\$4 trap\$4 nitride))
) same ((bl bitline bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line)
(word near (read\$3 writ\$3))
) and ((sonos monos mnos)
) and (((insulat\$5 dielectric oxide)
) near4 (oxidizing oxidized) (((("4173786" | "5168334" | "5284784" | "5349221" | "5717835" | "5768192" | "5988803" |
"5972751" | "8001889" | "8023085" | "8030871" | "8074915" | "8130453" | "8143808" | "8153487" | "8153471" |
"8157575" | "8159795".PN.) 6645801.URPN. ("5349221" | "5907171" | "6408960".PN.) 6541818.URPN. ("6458881" |
"6465303" | "2002/0086548".PN.) 6524913.URPN. ("4173786" | "5168334" | "5349221" | "5644533" | "5768182" |
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6488865.URPN.) ("20030109093" 6,670,671.pn.)

oct 2004

	#	+	Investor	Document	Issue	P	TIQs	Current	Current	XR	Retrieval	S	C	P	3	Image	Doc	P
1			Harari, Elijah	US 2003010	20030	3	Multi-state non-volatile integrated circuit me	438/200	257/E21.68			F	F	F	F	F	US 200301	F
2			Chen, Chien-	US 6784483	20040	1	Method for preventing hole and electron mov	257/317	257/315			F	F	F	F	F	US 678448	F
3			Sasago, Yesh	US 6870871	20031	3	Nonvolatile semiconductor memory device a	257/318	257/345			F	F	F	F	F	US 687087	F
4			Ramsbey, Ma	US 6645801	20031	1	Salicided gate for virtual ground arrays	438/216	257/314			F	F	F	F	F	US 664580	F
5			Ramsbey, Ma	US 6541816	20030	2	Planar structure for non-volatile memory dev	257/324	257/E21.67			F	F	F	F	F	US 654181	F
6			Lin, Hung-Sui	US 6524913	20030	7	Method of fabricating a non-volatile memory	438/281	438/287			F	F	F	F	F	US 652491	F
7			Eitan, Boaz	US 5966603	19991	9	NRQM fabrication method with a periphery p	438/258	257/E21.67			F	F	F	F	F	US 596660	F
8			Eitan, Boaz	US 5768192	19990	1	Non-volatile semiconductor memory cell utili	365/185	257/E29.30			F	F	F	F	F	US 576819	F
9			Lee, Thomas	US 2004020	20041	1	Dense arrays and charge storage devices	257/296				F	F	F	F	F	US 200402	F
10			Vyvoda, Mich	US 2004018	20040	8	Multiple-mode memory and method for formi	365/51				F	F	F	F	F	US 200401	F